

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3105	gate with angle with (recess\$2 groove\$2 open\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/15 17:23
L2	28	1 and SOI	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/15 17:45
L3	0	SOI AND substrate AND ((insulat\$3 oxide) near (layer film)) AND (isolat\$3 STI LOCOS) AND gate AND (main near surface) AND ((two dual pair twince) near (recess\$2 groove\$1 open\$3 hole\$1)) AND angle AND ((larger bigger greater) near2 "90") AND (semiconductor near (layer film)).CLM.	US-PGPUB; USPAT	OR	ON	2005/08/15 17:51